

NCEP0140AG

NCE N-Channel Super Trench Power MOSFET



The NCEP0140AG uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

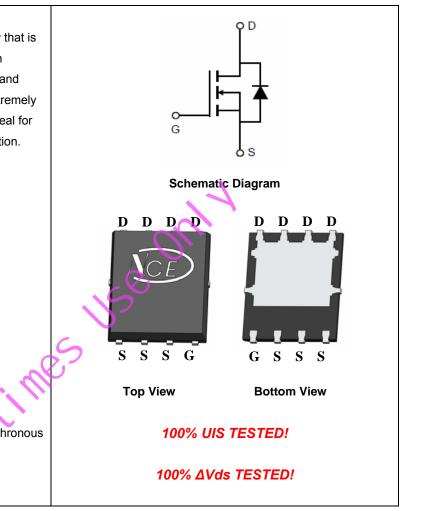
General Features

V_{DS} =100V,I_D =40A
R_{DS(ON)}=18mΩ (typical) @ V_{GS}=10V
R_{DS(ON)}=22mΩ (typical) @ V_{GS}=4.5V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0140AG	NCEP0140AG	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous (Silicon Limited)	Ι _D	40	А
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	28.3	A
Pulsed Drain Current (Package Limited)	I _{DM}	160	A
Maximum Power Dissipation	PD	50	W
Derating factor		0.4	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	200	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C







Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	2.5	°C/W
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Electrical Characteristics (T_c=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	2.0	2.8	V
Drain Source On State Desistence	Р	V _{GS} =10V, I _D =20A		18	23	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	22	27	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	-	35	-	S
Dynamic Characteristics (Note4)		0.				
Input Capacitance	Clss		-	1600	-	PF
Output Capacitance	Coss	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	139	-	PF
Reverse Transfer Capacitance	Crss		-	11	-	PF
Switching Characteristics (Note 4)		0.2				
Turn-on Delay Time	t _{d(on)}		-	6	-	nS
Turn-on Rise Time	t	V _{DD} =50V,I _D =20A	-	2	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	18	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Qg	V/ F0V/1 00A	-	26	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V,I _D =20A,	-	7.4		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.8		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =40A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	40	А
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A	-		26	nS
Reverse Recovery Charge	Qrr	di/dt = 500A/µs ^(Note3)			98	nC

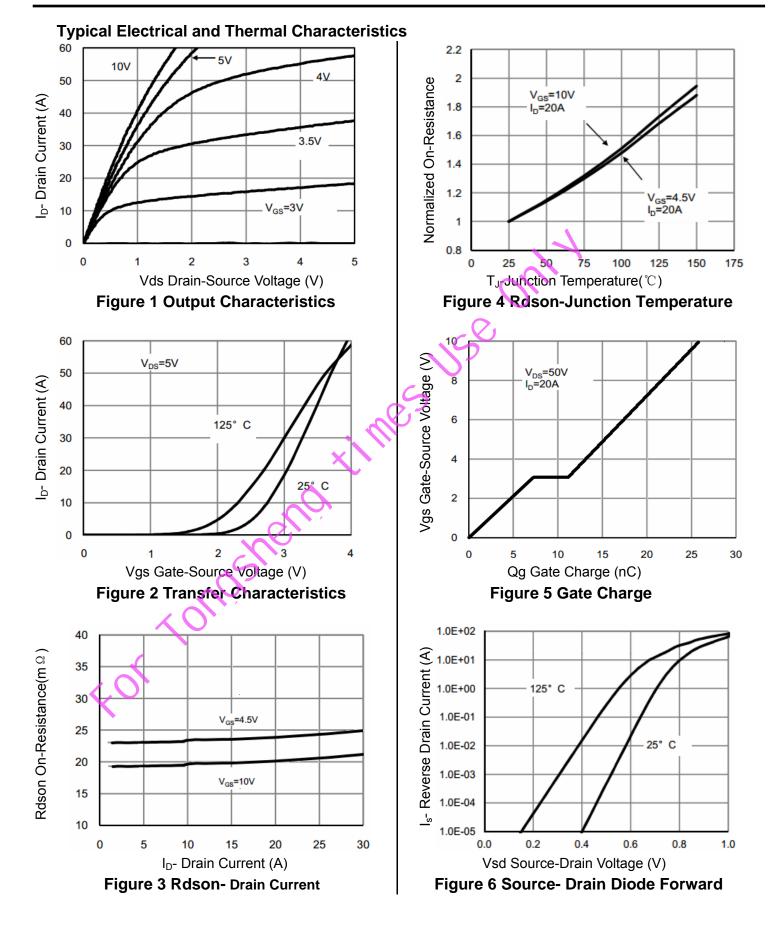
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ \! \mathrm{C}$,V_DD=20V,V_G=10V,L=0.5mH,Rg=25 Ω





Pb Free Product

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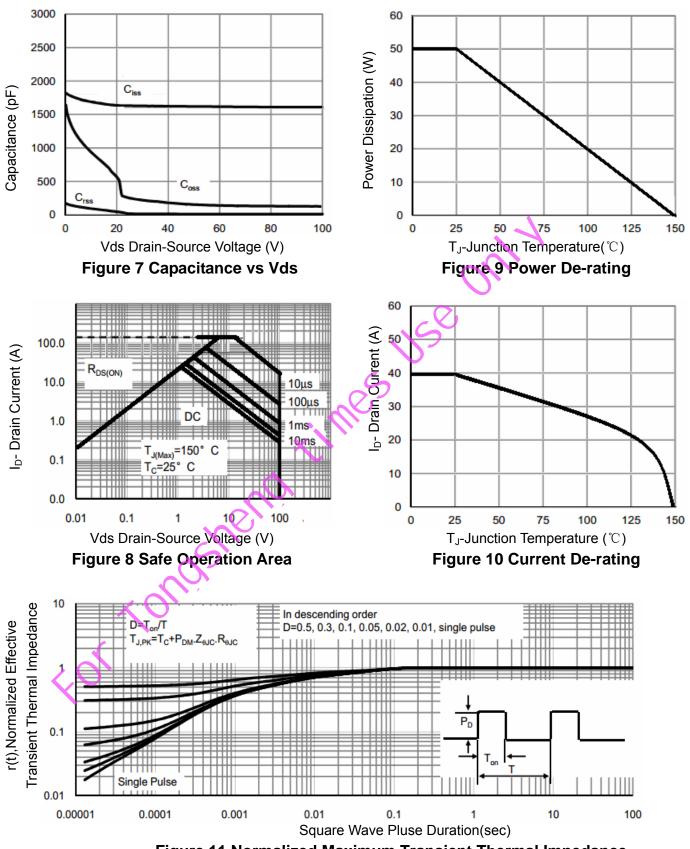
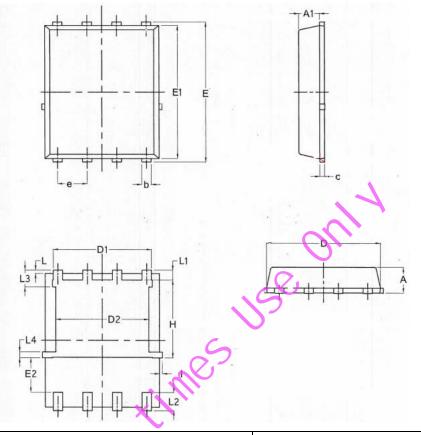


Figure 11 Normalized Maximum Transient Thermal Impedance





DFN5X6-8L Package Information



	Symbol	Dimensions In Millimeters			Dimensions In Inches			
		Min. 🜔	Nom.	Max.	Min.	Nom.	Max.	
	А	0.90	1.10	1.17	0.0354	0.0433	0.0461	
	A1	0.824	0.897	0.97	0.0324	0.0353	0.0382	
	b	0.33	0.41	0.50	0.0130	0.0161	0.0197	
	С	0.150	0.20	0.250	0.0059	0.0079	0.0098	
	D	4.80	4.90	5.00	0.1890	0.1929	0.1969	
	D1	3.91	4.22	4.36	0.1539	0.1661	0.1717	
	D2	3.85	4.00	4.15	0.1516	0.1575	0.1634	
\leq	E	5.90	60.5	6.15	0.2323	0.2382	0.2421	
	E1	5.65	5.76	5.85	0.2224	0.2268	0.2303	
	E2	1.10	/	/	0.0433	1	/	
	e	1.27 BSC			0.050 BSC			
	L	0.05	0.15	0.25	0.0020	0.0059	0.0098	
	L1	0.38	0.425	0.50	0.0150	0.0167	0.0197	
	L2	0.51	0.785	0.86	0.0201	0.0309	0.0339	
	L3	0.55	0.70	0.85	0.0217	0.0276	0.0335	
	L4	0.10	0.25	0.40	0.0039	0.0098	0.0157	
	Н	3.25	3.35	3.58	0.1280	0.1319	0.1409	
		0	1	0.18	0	/	0.0071	







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